

MJB44H11T4-A

Automotive-grade low voltage NPN power transistor

Datasheet - production data

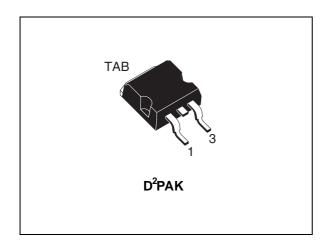
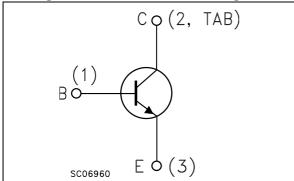


Figure 1. Internal schematic diagram



Features

- Designed for automotive applications and AEC- Q101 qualified
- Low collector-emitter saturation voltage
- · Fast switching speed

Applications

- · Power amplifier
- · Switching circuits

Description

This device is an NPN transistor manufactured using new low voltage planar technology with double metal process. The result is a transistor which boasts exceptionally high gain performance coupled with very low saturation voltage.

Table 1. Device summary

Order codes	Marking	Package	Packaging
MJB44H11T4-A	MJB44H11-A	D ² PAK	Tape and reel

1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-emitter voltage (I _B = 0)	80	V
V _{EBO}	Emitter-base voltage (I _C = 0)	5	V
I _C	Collector current	10	Α
I _{CM}	Collector peak current	20	Α
P _{TOT}	Total dissipation at T _{case} = 25 °C	50	W
TSTG	Storage temperature	-55 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Thermal resistance junction-case max	2.5	°C/W
R _{thJA}	Thermal resistance junction-ambient max	62.5	°C/W

2 Electrical characteristics

T_{case} = 25 °C; unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test con	ditions	Min.	Тур.	Max.	Unit
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage (I _B = 0)	I _C = 30 mA		80	-		V
I _{CES}	Collector cut-off current (V _{BE} = 0)	V _{CE} = 80 V			-	10	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 5 V			-	50	μΑ
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = 8 A	I _B = 0.4 A		1	1	V
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	I _C = 8 A	$I_B = 0.8 A$		1	1.5	V
h _{FE} ⁽¹⁾	DC current gain	I _C = 2 A	$V_{CE} = 1 V$	60	-		
	DO current gain	I _C = 4 A	$V_{CE} = 1 V$	40	-		

^{1.} Pulse test: pulse duration \leq 300 μ s, duty cycle \leq 2 %.

Electrical characteristics MJB44H11T4-A

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Ic (A)

| Ic MAX | PULSEO PERATION | 100 µs | 10

Figure 3. Derating curve

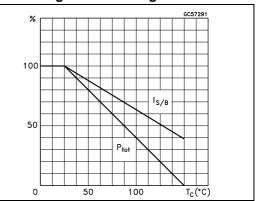
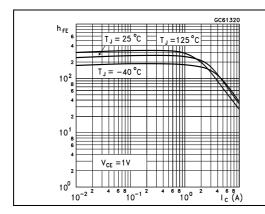
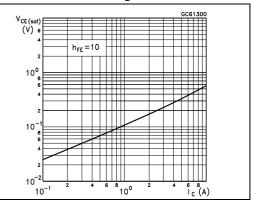


Figure 4. DC current gain

Figure 5. Collector-emitter saturation voltage





3 Package mechanical data

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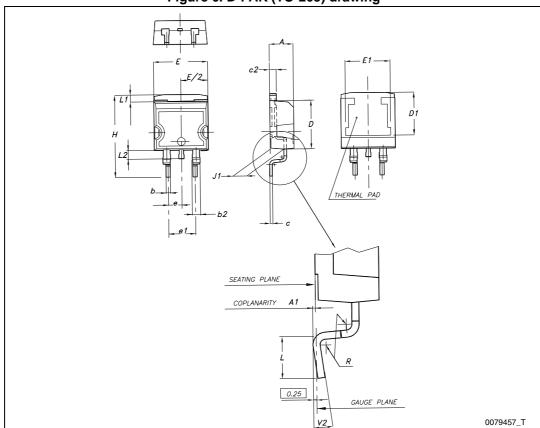


Figure 6. D²PAK (TO-263) drawing

Table 5. D²PAK (TO-263) mechanical data

Dim		mm	
Dim.	Min.	Тур.	Max.
А	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
С	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
Е	10		10.40
E1	8.50		
е		2.54	
e1	4.88		5.28
Н	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

16.90

12.20

16.90

5.08

9.75

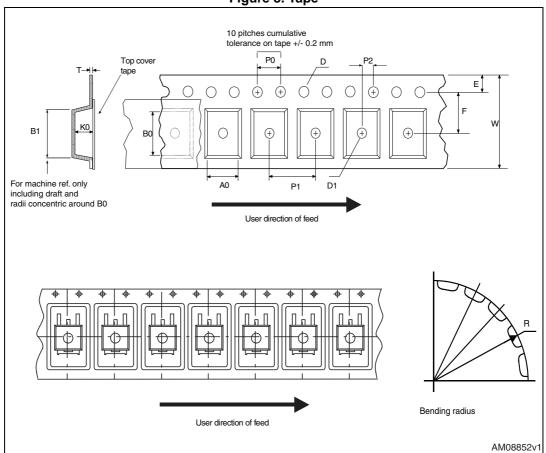
Figure 7. D²PAK footprint^(a)

a. All dimension are in millimeters



4 Packaging mechanical data

Figure 8. Tape



REEL DIMENSIONS 40mm min. Access hole At slot location В D С Tape slot in core for tape start 25 mm min. width G measured at hub Full radius AM08851v2

Figure 9. Reel

Table 6. D²PAK (TO-263) tape and reel mechanical data

Таре			Reel			
Dim.	mm		Dim.	mm		
Dilli.	Min.	Max.] Dilli.	Min.	Max.	
A0	10.5	10.7	Α		330	
В0	15.7	15.9	В	1.5		
D	1.5	1.6	С	12.8	13.2	
D1	1.59	1.61	D	20.2		
Е	1.65	1.85	G	24.4	26.4	
F	11.4	11.6	N	100		
K0	4.8	5.0	Т		30.4	
P0	3.9	4.1				
P1	11.9	12.1		Base qty	1000	
P2	1.9	2.1		Bulk qty	1000	
R	50					
Т	0.25	0.35				
W	23.7	24.3				

Revision history MJB44H11T4-A

5 Revision history

Table 7. Document revision history

Date	Revision	Changes
12-May-2014	1	Initial release.

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